

The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

Applicants submit that all references submitted with this disclosure were first cited in a communication from a foreign patent office dated January 10, 2005, which communication is enclosed, not more than three months prior to the filing of this Supplemental Information Disclosure Statement.

If the sum of \$180.00 is due under 37 CFR § 1.17(p) pursuant to § 1.97, the Commissioner is hereby authorized to charge this fee, and any other fee necessary to make this submission timely, to the Deposit Account No. 20-0782/AMAT/2592.C9/KMT.

Respectfully submitted,



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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1

of 1

Application Number

10/789,209

Filing Date

FEBRUARY 27, 2004

First Named Inventor

GAILLARD, ET AL.

Group Art Unit

2818

Examiner Name

DAVID NHU

Attorney Docket Number

AMAT/2592.C9/DSM/LOW K/JW

Submission Date

3/8, 2005

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
	C1	BAKLI, ET AL., "Materials and Processing for .025 μ m Multilevel Interconnect," Microelectronic Engineering 33 (1997) pp. 175-188.	
	C2	BHAN, ET AL., "Deposition of Stable Low K and High Deposition Rate SiF ₄ -Doped TEOS Fluorinated Silicon Dioxide (SiOF) Films," Thin Solid Films 308-309 (1997) pp. 507-511.	
	C3	C.F. LIN, ET AL., "Improved Ozone-Tetraethoxysilane Oxide Reliability for Deep Submicron Inter-Metal Dielectric Applications by Deposition of a Silane-Based Oxide Underlayer," Thin Solid Films 308-309 (1997) pp. 621-626.	
	C4	European Search Report from European Patent Office for 99906897.6 (2592.EP), dated 01/10/2005.	
	C5		
	C6		
	C7		
	C8		
	C9		
	C10		
	C11		

Examiner

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.